

## Insulated Gate Bipolar Transistor (Ultrafast Speed IGBT), 100 A


**SOT-227**

PRIMARY CHARACTERISTICS	
$V_{CES}$	600 V
$V_{CE(on)}$ (typical)	1.92 V
$V_{GE}$	15 V
$I_C$	100 A
Speed	8 kHz to 30 kHz
Package	SOT-227
Circuit configuration	Single switch no diode

**FEATURES**

- Ultrafast: optimized for minimum saturation voltage and speed up to 30 kHz in hard switching, > 200 kHz in resonant mode
- Very low conduction and switching losses
- Fully isolate package (2500 V<sub>AC</sub>/RMS)
- Very low internal inductance ( $\leq 5$  nH typical)
- Industry standard outline
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS  
COMPLIANT**
**BENEFITS**

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Lower overall losses available at frequencies = 20 kHz
- Easy to assemble and parallel
- Direct mounting to heatsink
- Lower EMI, requires less snubbing
- Plug-in compatible with other SOT-227 packages

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{CES}$		600	V
Continuous collector current	$I_C$	$T_C = 25\text{ }^\circ\text{C}$	200	A
		$T_C = 100\text{ }^\circ\text{C}$	100	
Pulsed collector current	$I_{CM}$		400	
Clamped inductive load current	$I_{LM}$	$V_{CC} = 80\% (V_{CES})$ , $V_{GE} = 20\text{ V}$ , $L = 10\text{ }\mu\text{H}$ , $R_g = 2.0\text{ }\Omega$ , see fig. 13a	400	
Gate to emitter voltage	$V_{GE}$		$\pm 20$	V
Reverse voltage avalanche energy	$E_{ARV}$	Repetitive rating; pulse width limited by maximum junction temperature	160	mJ
RMS isolation voltage	$V_{ISOL}$	Any terminal to case, $t = 1\text{ min}$	2500	V
Maximum power dissipation	$P_D$	$T_C = 25\text{ }^\circ\text{C}$	500	W
		$T_C = 100\text{ }^\circ\text{C}$	200	
Operating junction and storage temperature range	$T_J, T_{Stg}$		-55 to +150	$^\circ\text{C}$
Mounting torque		6-32 or M3 screw	1.3 (12)	Nm (lbf.in)

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	$T_J, T_{Stg}$		-55	-	150	$^\circ\text{C}/\text{W}$
Thermal resistance, junction to case	$R_{thJC}$		-	-	0.25	
Thermal resistance case to heatsink	$R_{thCS}$	Flat, greased, surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style			SOT-227			



<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$ , $I_C = 250\text{ }\mu\text{A}$	600	-	-	V
Emitter to collector breakdown voltage	$V_{(BR)ECS}$	$V_{GE} = 0\text{ V}$ , $I_C = 1.0\text{ A}$ Pulse width $\leq 80\text{ }\mu\text{s}$ ; duty factor $\leq 0.1\%$	18	-	-	
Temperature coefficient of breakdown voltage	$\Delta V_{(BR)CES}/\Delta T_J$	$V_{GE} = 0\text{ V}$ , $I_C = 10\text{ mA}$	-	0.38	-	V/ $^\circ\text{C}$
Collector to emitter saturation voltage	$V_{CE(on)}$	$I_C = 100\text{ A}$	-	1.60	1.9	V
		$I_C = 200\text{ A}$	-	1.92	-	
		$I_C = 100\text{ A}$ , $T_J = 150\text{ }^\circ\text{C}$	-	1.54	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$ , $I_C = 250\text{ }\mu\text{A}$	3.0	-	6.0	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$ , $I_C = 2.0\text{ mA}$	-	-11	-	mV/ $^\circ\text{C}$
Forward transconductance	$g_{fe}$	$V_{CE} = 100\text{ V}$ , $I_C = 100\text{ A}$ Pulse width $5.0\text{ }\mu\text{s}$ , single shot	79	-	-	S
Zero gate voltage collector current	$I_{CES}$	$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$	-	-	1.0	mA
		$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$	-	-	10	
Gate to emitter leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}$	-	-	$\pm 250$	nA

<b>SWITCHING CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	$Q_g$	$I_C = 100\text{ A}$	-	770	1200	nC	
Gate-emitter charge (turn-on)	$Q_{ge}$	$V_{CC} = 400\text{ V}$	-	100	150		
Gate-collector charge (turn-on)	$Q_{gc}$	$V_{GE} = 15\text{ V}$ ; See fig. 8	-	260	380		
Turn-on delay time	$t_{d(on)}$	$T_J = 25\text{ }^\circ\text{C}$ $I_C = 100\text{ A}$ $V_{CC} = 480\text{ V}$ $V_{GE} = 15\text{ V}$ $R_g = 2.0\text{ }\Omega$	-	54	-	ns	
Rise time	$t_r$		-	79	-		
Turn-off delay time	$t_{d(off)}$		-	130	200		
Fall time	$t_f$		-	300	450		
Turn-on switching loss	$E_{on}$		-	0.98	-		mJ
Turn-off switching loss	$E_{off}$	Energy losses include "tail"	-	3.48	-		
Total switching loss	$E_{ts}$	See fig. 9, 10, 14	-	4.46	7.6		
Turn-on delay time	$t_{d(on)}$	$T_J = 150\text{ }^\circ\text{C}$ $I_C = 100\text{ A}$ , $V_{CC} = 480\text{ V}$ $V_{GE} = 15\text{ V}$ , $R_g = 2.0\text{ }\Omega$	-	56	-	ns	
Rise time	$t_r$		-	75	-		
Turn-off delay time	$t_{d(off)}$		-	160	-		
Fall time	$t_f$		Energy losses include "tail"	-	460		-
Total switching loss	$E_{ts}$		See fig. 10, 11, 14	-	7.24		-
Internal emitter inductance	$L_E$	Measured 5 mm from package	-	5.0	-	nH	
Input capacitance	$C_{ies}$	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$ $f = 1.0\text{ MHz}$ ; See fig. 7	-	16 500	-	pF	
Output capacitance	$C_{oes}$		-	1000	-		
Reverse transfer capacitance	$C_{res}$		-	200	-		

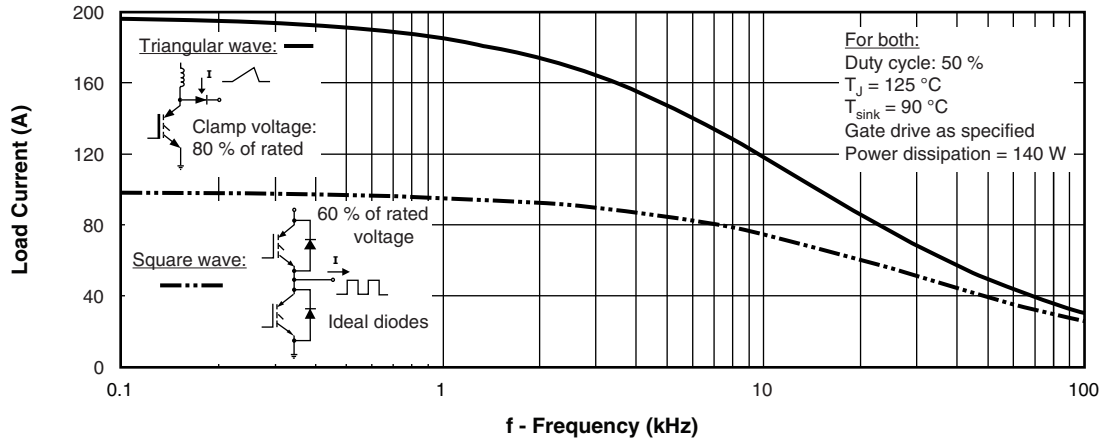


Fig. 1 - Typical Load Current vs. Frequency  
(Load Current =  $I_{RMS}$  of Fundamental)

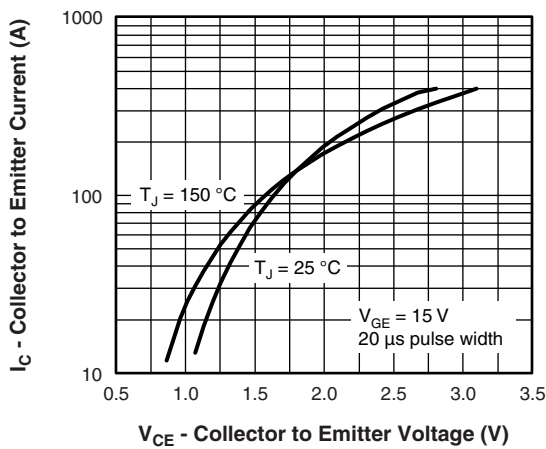


Fig. 2 - Typical Output Characteristics

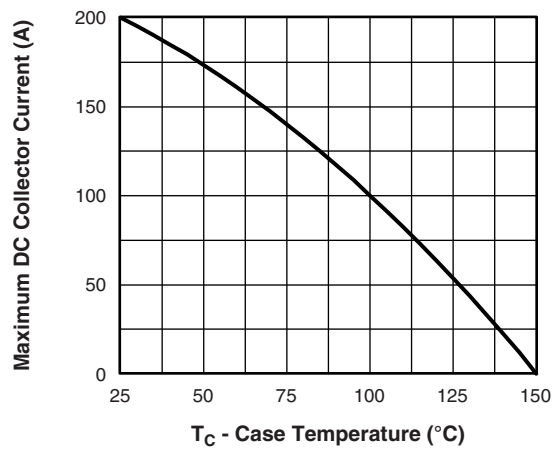


Fig. 4 - Maximum Collector Current vs. Case Temperature

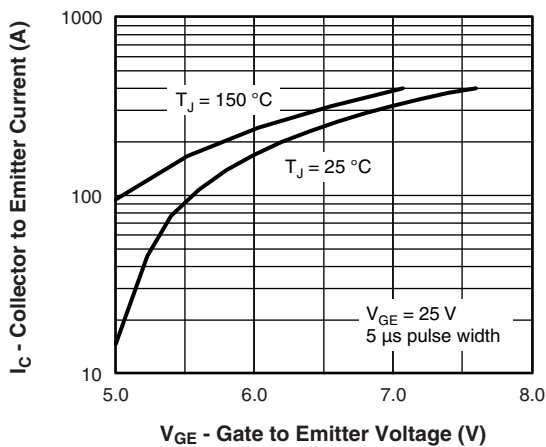


Fig. 3 - Typical Transfer Characteristics

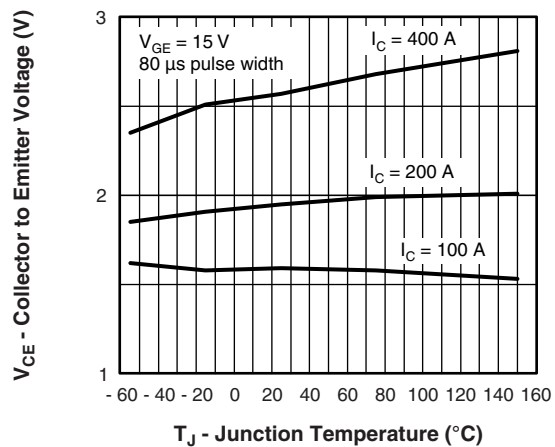


Fig. 5 - Typical Collector to Emitter Voltage vs. Junction Temperature

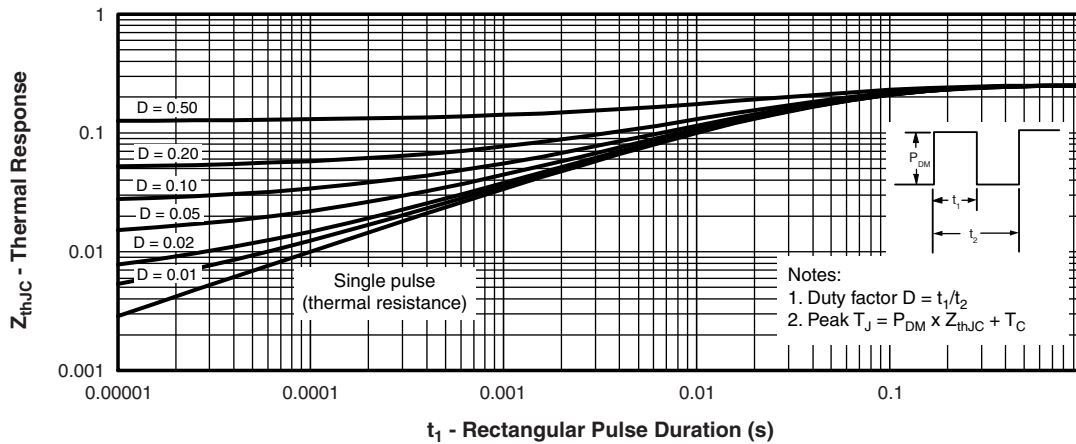


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction to Case

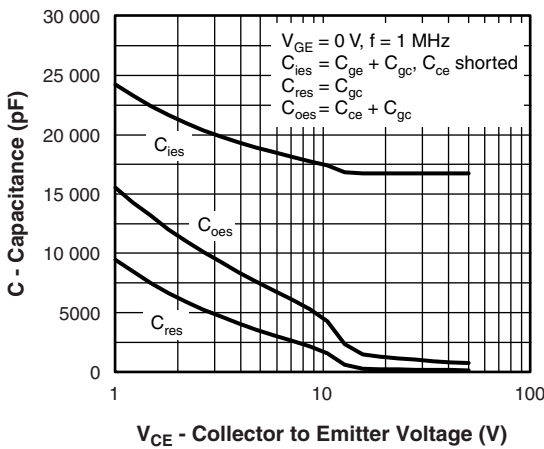


Fig. 7 - Typical Capacitance vs. Collector to Emitter Voltage

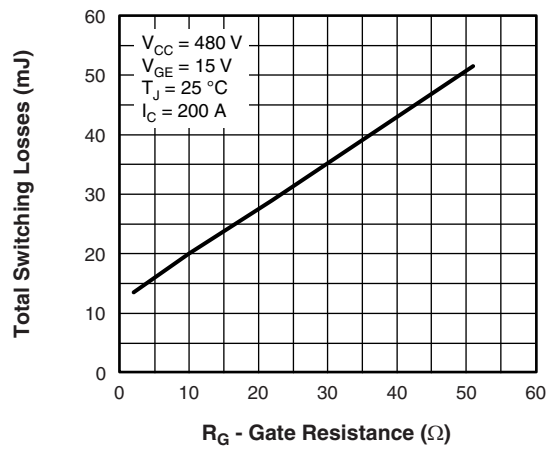


Fig. 9 - Typical Switching Losses vs. Gate Resistance

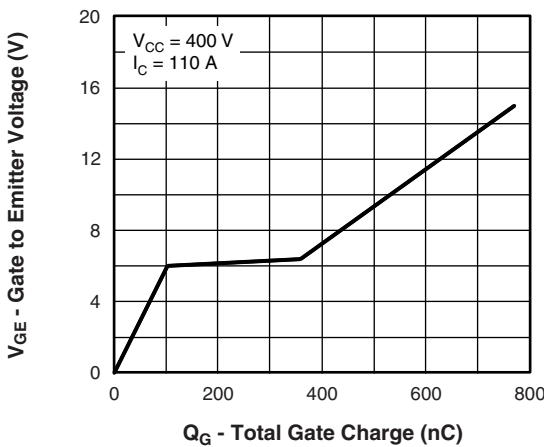


Fig. 8 - Typical Gate Charge vs. Gate to Emitter Voltage

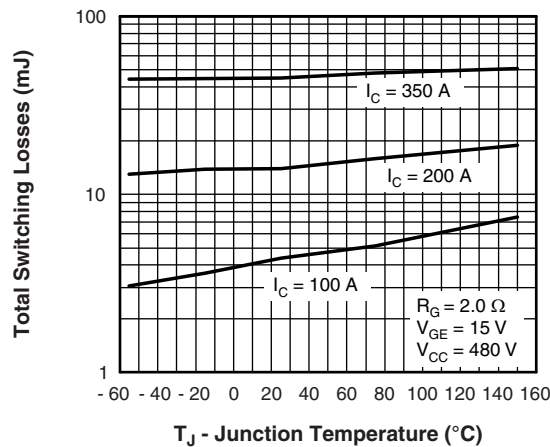


Fig. 10 - Typical Switching Losses vs. Junction Temperature

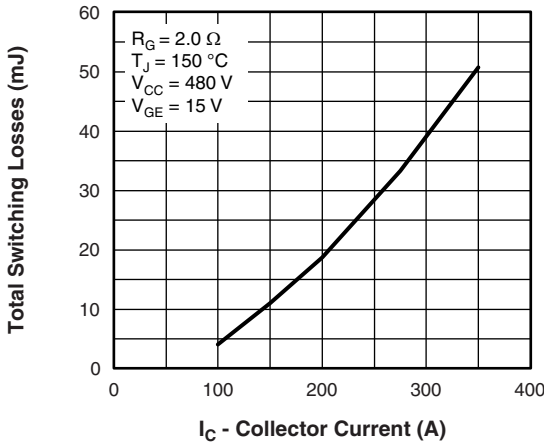


Fig. 11 - Typical Switching Losses vs. Collector Current

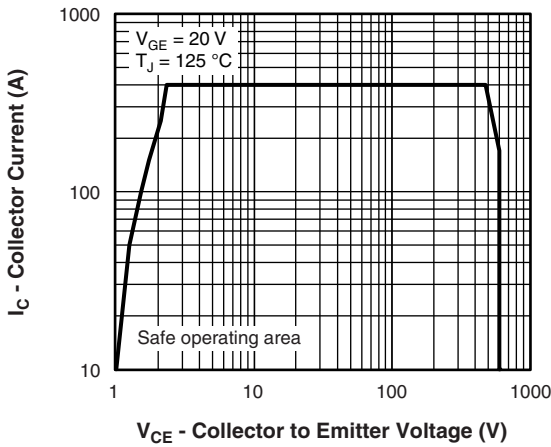
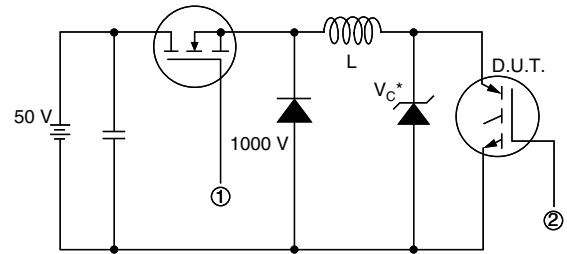


Fig. 12 - Turn-Off SOA



\* Driver same type as D.U.T.;  $V_C = 80\%$  of  $V_{CE}$  (max)

**Note:** Due to the 50 V power supply, pulse width and inductor will increase to obtain rated  $I_d$

Fig. 13a - Clamped Inductive Load Test Circuit

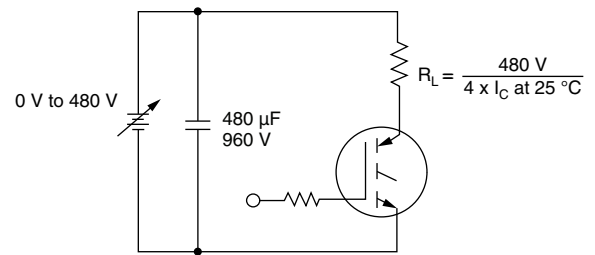
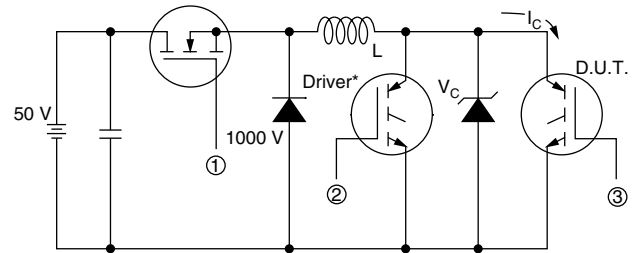


Fig. 13b - Pulsed Collector Current Test Circuit



\* Driver same type as D.U.T.,  $V_C = 480 \text{ V}$

Fig. 14a - Switching Loss Test Circuit

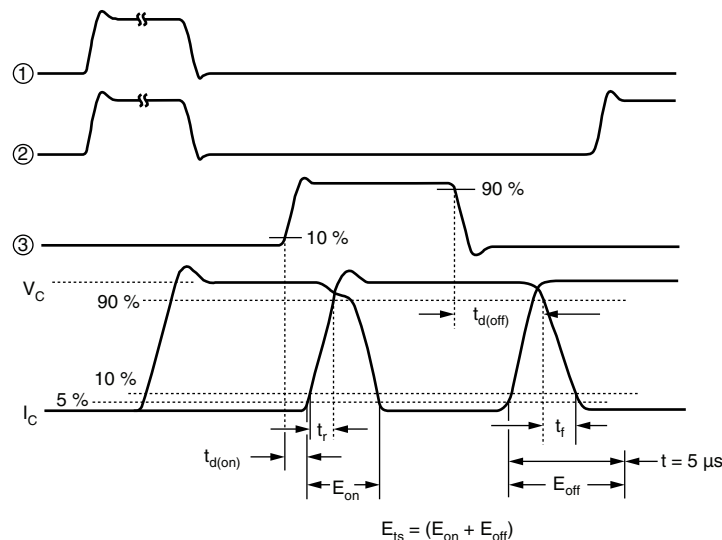
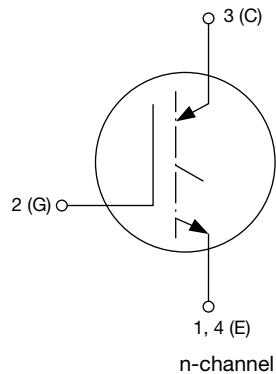


Fig. 14b - Switching Loss Waveforms

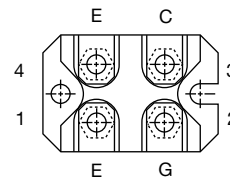
**ORDERING INFORMATION TABLE**

Device code	<b>VS-</b>	<b>G</b>	<b>A</b>	<b>200</b>	<b>S</b>	<b>A</b>	<b>60</b>	<b>U</b>	<b>P</b>
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - Insulated gate bipolar transistor (IGBT)
- 3** - Generation 4, IGBT silicon, DBC construction
- 4** - Current rating (200 = 200 A)
- 5** - Single switch no diode
- 6** - SOT-227
- 7** - Voltage rating (60 = 600 V)
- 8** - Speed/type (U = ultrafast)
- 9** -
  - None = standard production
  - P = lead (Pb)-free

**CIRCUIT CONFIGURATION**


Lead assignment

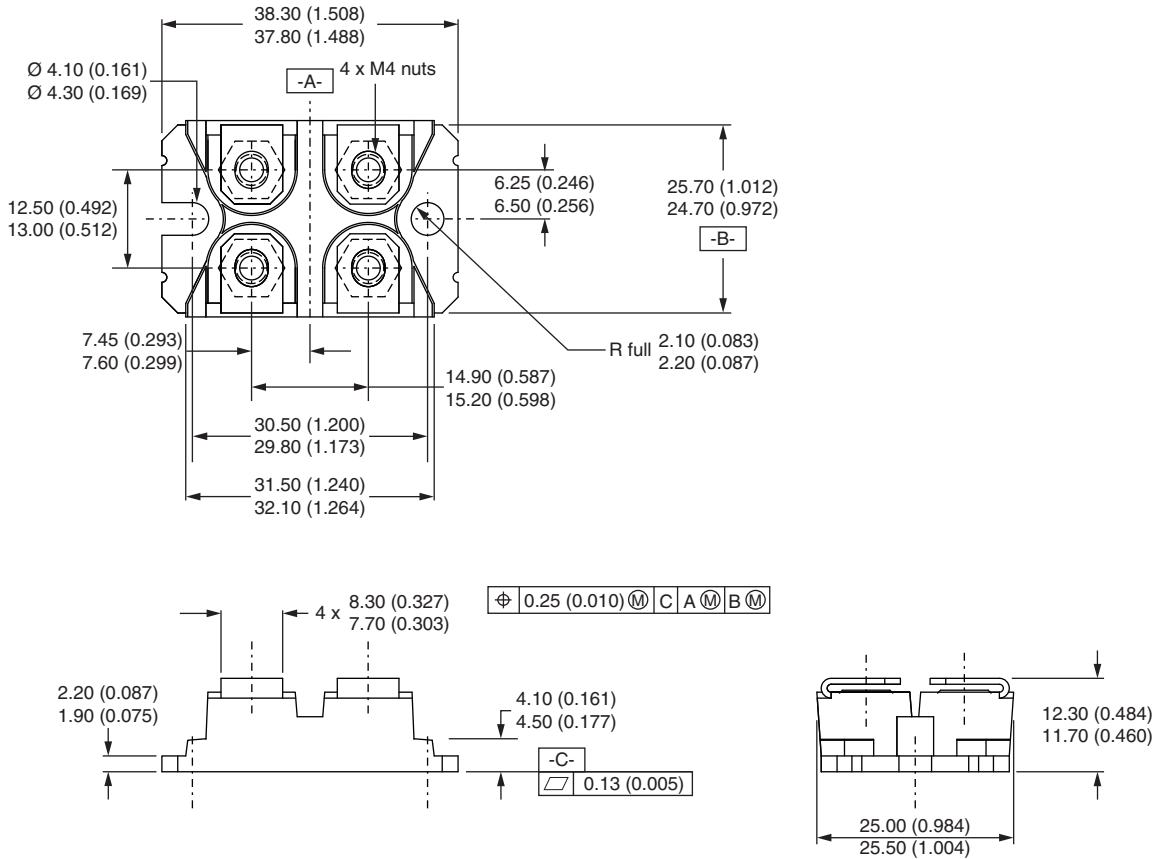

**LINKS TO RELATED DOCUMENTS**

Dimensions	<a href="http://www.vishay.com/doc?95425">www.vishay.com/doc?95425</a>
Packaging information	<a href="http://www.vishay.com/doc?95423">www.vishay.com/doc?95423</a>



### SOT-227 Generation II

**DIMENSIONS** in millimeters (inches)



**Note**

- Controlling dimension: millimeter



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